



- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

#### Product Summary

BVDSS	RDSON	ID
-20V	75mΩ	-3A

#### Description

The S50 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The S50 meet the RoHS and Green Product requirement with full function reliability approved.

#### SOT23 Pin Configuration

#### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-20	V
V <sub>GS</sub>	Gate-Source Voltage	±12	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-3	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-2.4	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-12	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	1	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

#### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>	---	125	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	80	°C/W



Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-4.5V, I_D=-3A$	---	---	95	m $\Omega$
		$V_{GS}=-2.5V, I_D=-2A$	---	---	110	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.3	-0.5	-1.0	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-16V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	$\mu A$
		$V_{DS}=-16V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=-5V, I_D=-3A$	---	12.2	---	S
$Q_g$	Total Gate Charge (-4.5V)	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-3A$	---	10.1	---	nC
$Q_{gs}$	Gate-Source Charge		---	1.21	---	
$Q_{gd}$	Gate-Drain Charge		---	2.46	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-10V, V_{GS}=-4.5V, R_G=3.3\Omega, I_D=-3A$	---	5.6	---	ns
$T_r$	Rise Time		---	32.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	45.6	---	
$T_f$	Fall Time		---	29.2	---	
$C_{iss}$	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	677	---	pF
$C_{oss}$	Output Capacitance		---	82	---	
$C_{rss}$	Reverse Transfer Capacitance		---	73	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V$ , Force Current	---	---	-3	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



### Typical Characteristics

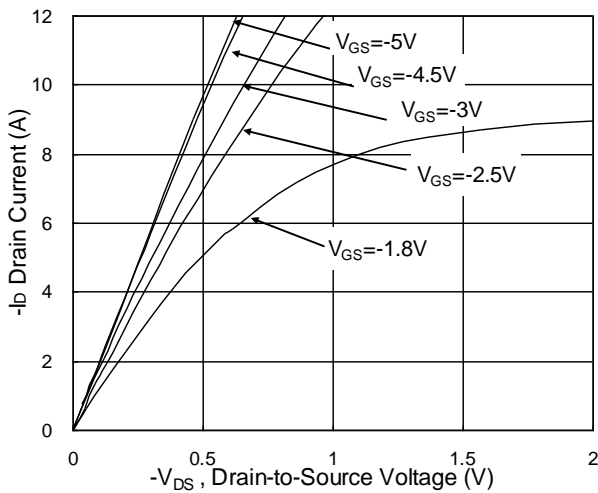


Fig.1 Typical Output Characteristics

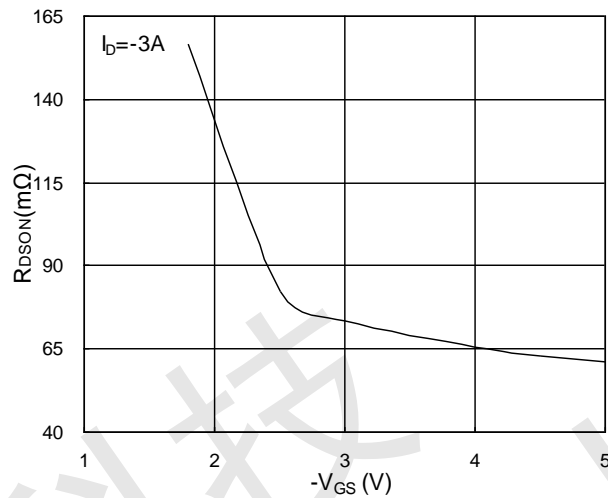


Fig.2 On-Resistance vs. Gate-Source Voltage

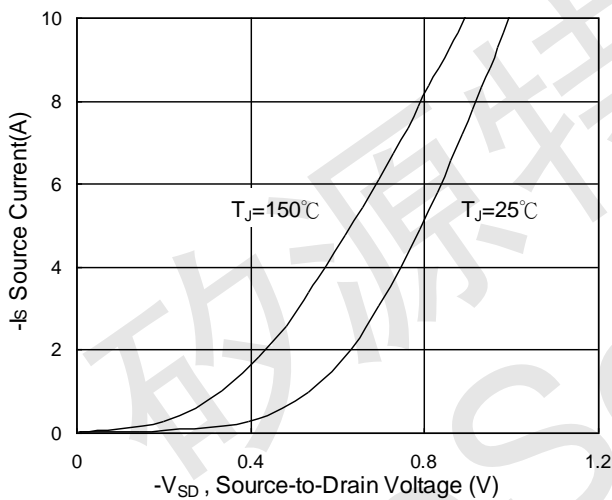


Fig.3 Forward Characteristics of Reverse

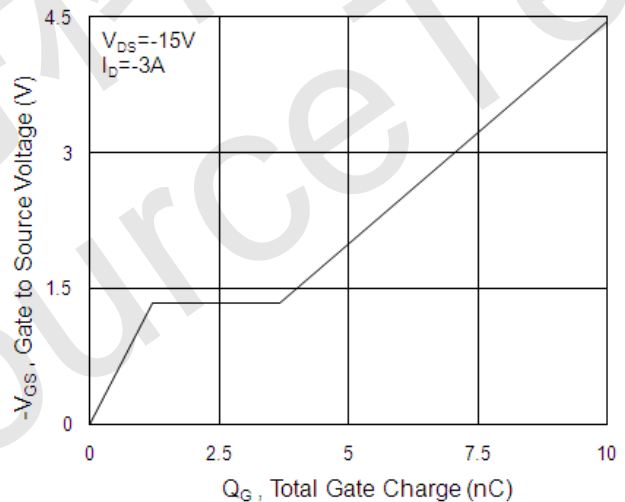


Fig.4 Gate-Charge Characteristics

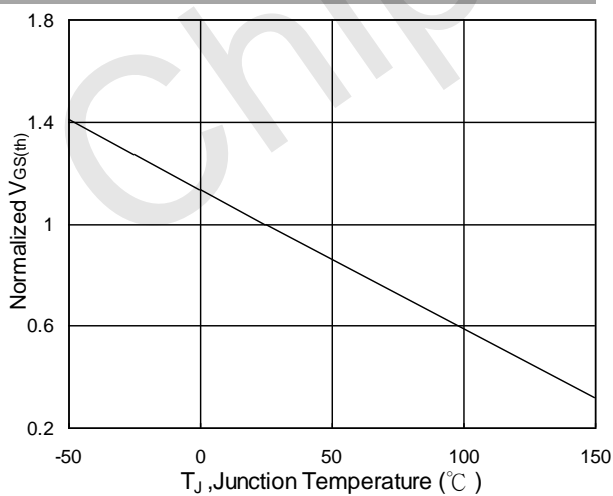


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

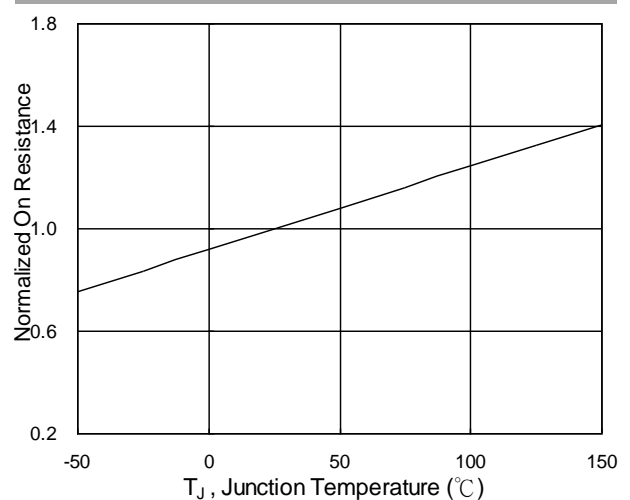


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

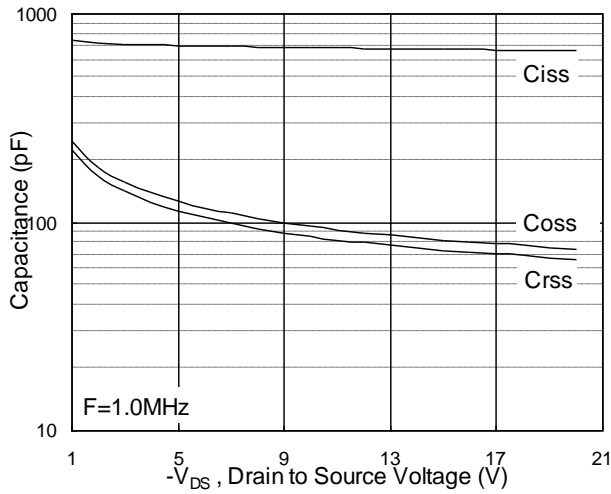


Fig.7 Capacitance

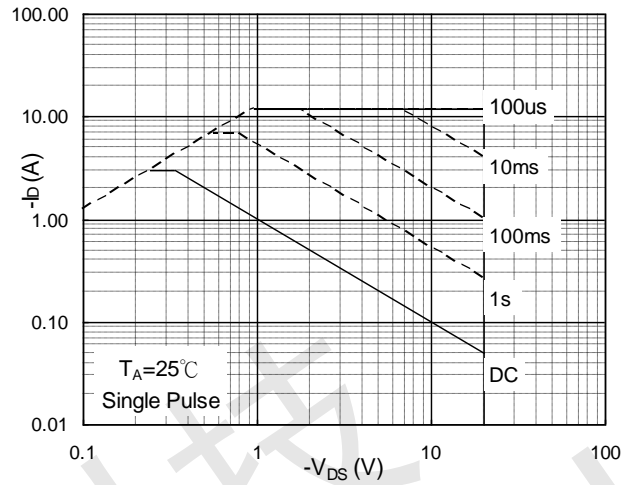


Fig.8 Safe Operating Area

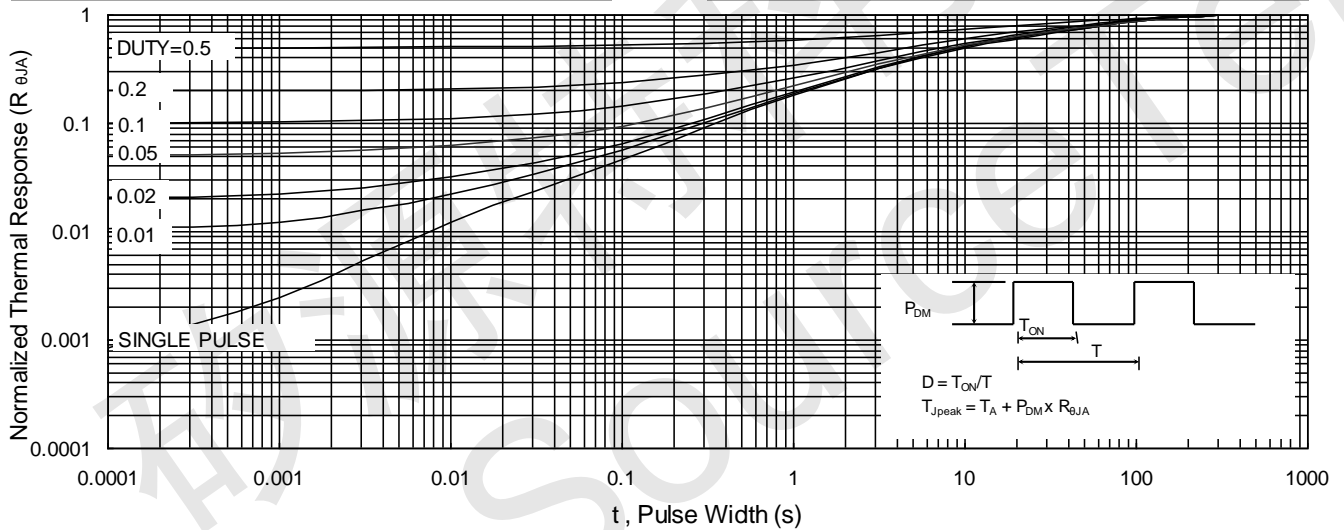


Fig.9 Normalized Maximum Transient Thermal Impedance

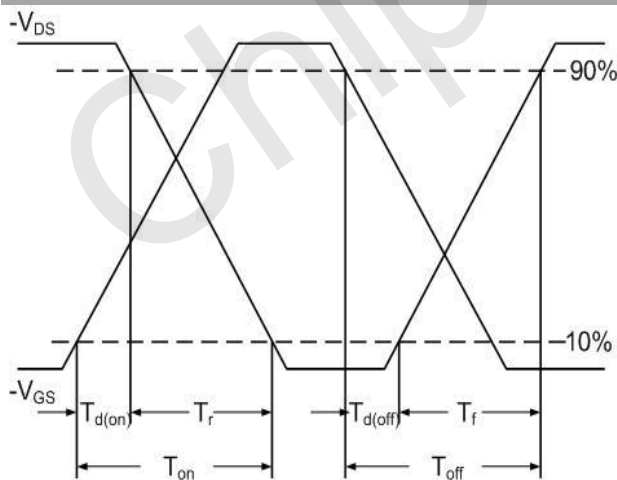


Fig.10 Switching Time Waveform

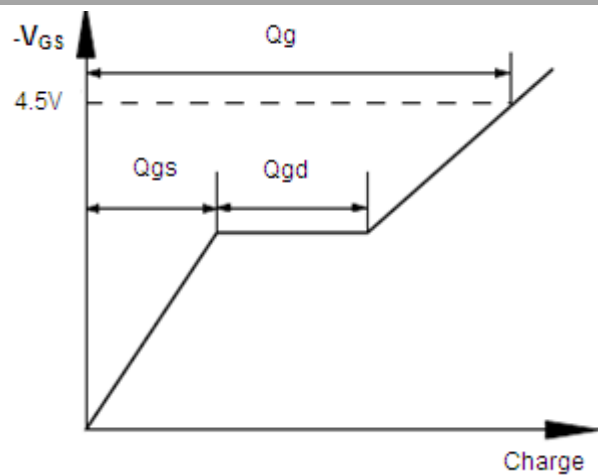


Fig.11 Gate Charge Waveform